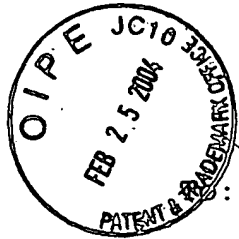


TSMC-01-1488



February 19, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/666,359 09/19/03 |

Chi-Chun Chen et al.

METHOD OF FORMING AN ULTRATHIN
NITRIDE/OXIDE STACK AS A GATE
DIELECTRIC

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
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Stephen B. Ackerman, Reg.# 37761

Signature/Date

Stephen B. Ackerman 2/23/04

TSMC-01-1488

Taiwan Patent NP-0763-TW discusses the step coverage capability of TEOS-SiO₂ being excellent and a SiO₂LPCVD reaction mainly using TEOS being widely adopted in the semiconductor industry.

Sincerely,

Stephen B. Ackerman,
Reg. No. 37761

Form PTO-1449

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several shouts if necessary)

Dollar Market (Copper)

TSmc-01-1488

Agitation Number

10/666,359

London

Chi-Chun Chen et al.

Filing Date

09/19/03

Group Art Unit

U. S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
	NP-0763-TW	6/17/03	Taiwan				

OTHER DOCUMENTS (Including Author, Title, Date, Portion or Pages, Etc.)

EXPLANATION

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.